

K E J Goh

List of Publications by Year in descending order

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19
papers

335
citations

840776

11
h-index

888059

17
g-index

19
all docs

19
docs citations

19
times ranked

327
citing authors

#	ARTICLE	IF	CITATIONS
1	Patterning of sub-1 nm dangling-bond lines with atomic precision alignment on H:Si(100) surface at room temperature. <i>Nanotechnology</i> , 2012, 23, 275301.	2.6	11
2	Study of automatic recovery on the metal nanocrystal-based Al ₂ O ₃ /SiO ₂ gate stack. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	0
3	Using patterned H-resist for controlled three-dimensional growth of nanostructures. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	9
4	Tri-Level Resistive Switching in Metal-Nanocrystal-Based $\text{Al}_2\text{O}_3/\text{SiO}_2$ Gate Stack. <i>IEEE Transactions on Electron Devices</i> , 2010, 57, 3001-3005.	3.0	7
5	Impact of Si growth rate on coherent electron transport in Si:P delta-doped devices. <i>Applied Physics Letters</i> , 2009, 95, 142104.	3.3	11
6	Enhancing electron transport in Si:P delta-doped devices by rapid thermal anneal. <i>Applied Physics Letters</i> , 2008, 93, 142105.	3.3	13
7	Electron-electron interactions in highly disordered two-dimensional systems. <i>Physical Review B</i> , 2008, 77, .	3.2	40
8	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. <i>Applied Physics Letters</i> , 2008, 92, 052101.	3.3	12
9	Morphology and electrical conduction of Si:P $\hat{\nu}$ -doped layers on vicinal Si(001). <i>Journal of Applied Physics</i> , 2008, 104, 066104.	2.5	10
10	Use of a scanning electron microscope to pattern large areas of a hydrogen resist for electrical contacts. <i>Journal of Applied Physics</i> , 2007, 102, .	2.5	8
11	Use of low-temperature Hall effect to measure dopant activation: Role of electron-electron interactions. <i>Physical Review B</i> , 2007, 76, .	3.2	6
12	Electronic properties of atomically abrupt tunnel junctions in silicon. <i>Physical Review B</i> , 2007, 75, .	3.2	31
13	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. <i>Nanotechnology</i> , 2007, 18, 044023.	2.6	24
14	Electrical properties of atomically controlled Si:P nanowires created by scanning probe microscopy. <i>AIP Conference Proceedings</i> , 2007, , .	0.4	0
15	Influence of doping density on electronic transport in degenerate Si:P $\hat{\nu}$ -doped layers. <i>Physical Review B</i> , 2006, 73, .	3.2	62
16	Relevance of phosphorus incorporation and hydrogen removal for Si:P $\hat{\nu}$ -doped layers fabricated using phosphine. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 1002-1005.	1.8	10
17	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. <i>Nanotechnology</i> , 2005, 16, 2446-2449.	2.6	26
18	Effective removal of hydrogen resists used to pattern devices in silicon using scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2005, 86, 143116.	3.3	11

#	ARTICLE	IF	CITATIONS
19	Effect of encapsulation temperature on Si:P \hat{I} -doped layers. Applied Physics Letters, 2004, 85, 4953-4955.	3.3	44